



STGP12NB60H

N-CHANNEL 12A - 600V TO-220 PowerMESH™ IGBT

PRELIMINARY DATA

TYPE	V _{CES}	V _{CE(sat)}	I _C
STGP12NB60H	600 V	< 2.8 V	12 A

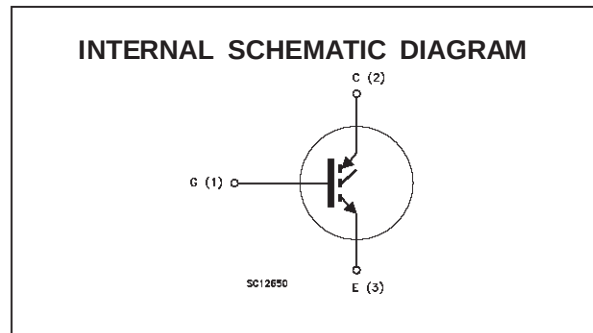
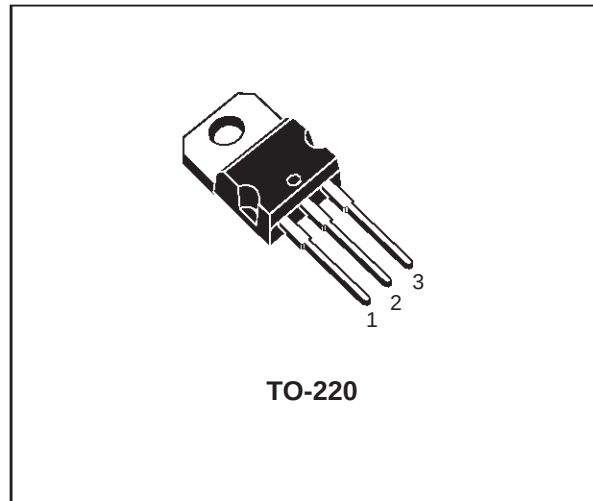
- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{CESAT})
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- VERY HIGH FREQUENCY OPERATION
- OFF LOSSES INCLUDE TAIL CURRENT

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "H" identifies a family optimized to achieve very low switching times for high frequency applications (<120kHz).

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS AND PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES
- UPS



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{ECR}	Emitter-Collector Voltage	20	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at T _c = 25 °C	24	A
I _C	Collector Current (continuous) at T _c = 100 °C	12	A
I _{CM} (•)	Collector Current (pulsed)	96	A
P _{tot}	Total Dissipation at T _c = 25 °C	100	W
	Derating Factor	0.8	W/°C
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(•) Pulse width limited by safe operating area

STGP12NB60H

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	1.25	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W
R _{thc-h}	Thermal Resistance Case-heatsink	Typ	0.5	°C/W

ELECTRICAL CHARACTERISTICS (T_j = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collector-Emitter Breakdown Voltage	I _C = 250 µA V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating T _j = 25 °C V _{CE} = Max Rating T _j = 125 °C			10 100	µA µA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20 V V _{CE} = 0			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} I _C = 250 µA	3		5	V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{GE} = 15 V I _C = 12 A V _{GE} = 15 V I _C = 12 A T _j = 125 °C		2.0 1.7	2.8	V V

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs}	Forward Transconductance	V _{CE} = 25 V I _C = 12 A		9.5		S
C _{ies} C _{oes} C _{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{CE} = 25 V f = 1 MHz V _{GE} = 0		950 120 27		pF pF pF
Q _G Q _{GE} Q _{GC}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	V _{CE} = 480 V I _C = 12 A V _{GE} = 15 V		68 10 30		nC nC nC
I _{CL}	Latching Current	V _{clamp} = 480 R _G = 10 Ω T _j = 150 °C	48			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r	Delay Time Rise Time	V _{CC} = 480 V I _C = 12 A V _{GE} = 15 V R _G = 10 Ω		5 46		ns ns
(di/dt) _{on}	Turn-on Current Slope	V _{CC} = 480 V I _C = 12 A R _G = 10 Ω V _{GE} = 15 V		1000		A/µs
E _{on}	Turn-on Switching Losses	T _j = 125 °C		290		µJ

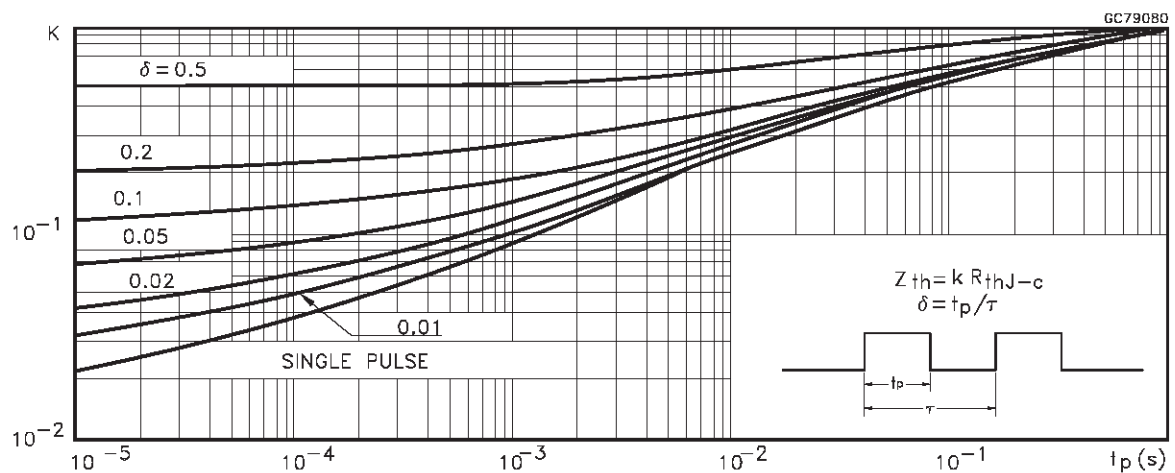
ELECTRICAL CHARACTERISTICS (continued)**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c	Cross-Over Time	$V_{CC} = 480 \text{ V}$ $I_C = 12 \text{ A}$		150		ns
$t_r(V_{off})$	Off Voltage Rise Time	$R_{GE} = 10 \text{ } \Omega$ $V_{GE} = 15 \text{ V}$		27		ns
$t_d(off)$	Delay Time			76		ns
t_f	Fall Time			92		ns
$E_{off(**)}$	Turn-off Switching Loss			0.21		mJ
E_{ts}	Total Switching Loss			0.49		mJ
t_c	Cross-Over Time	$V_{CC} = 480 \text{ V}$ $I_C = 12 \text{ A}$		230		ns
$t_r(V_{off})$	Off Voltage Rise Time	$R_{GE} = 10 \text{ } \Omega$ $V_{GE} = 15 \text{ V}$		76		ns
$t_d(off)$	Delay Time	$T_j = 125 \text{ } ^\circ\text{C}$		95		ns
t_f	Fall Time			200		ns
$E_{off(**)}$	Turn-off Switching Loss			0.45		mJ
E_{ts}	Total Switching Loss			0.74		mJ

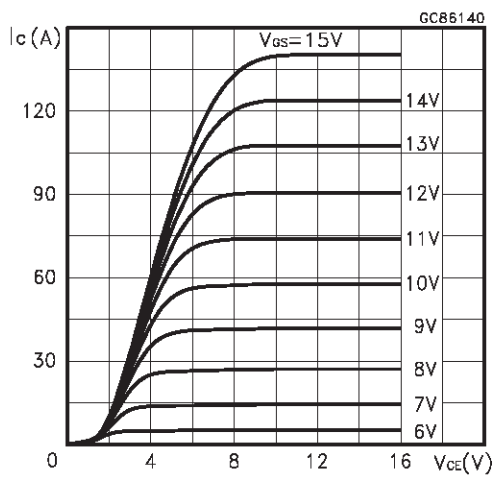
(●) Pulse width limited by max. junction temperature

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

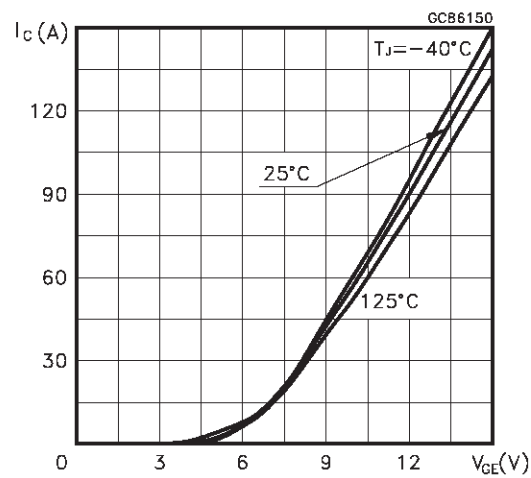
(**) Losses Include Also The Tail (Jedec Standardization)

Thermal Impedance

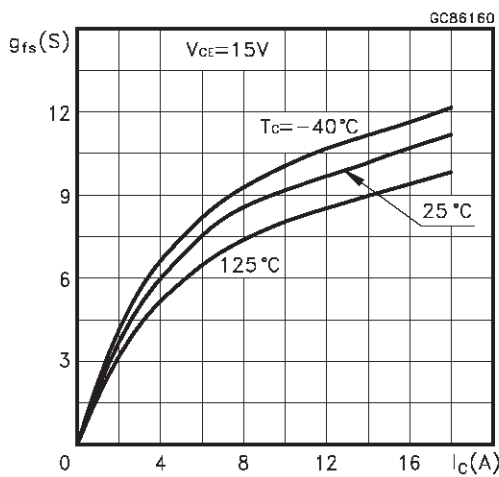
Output Characteristics



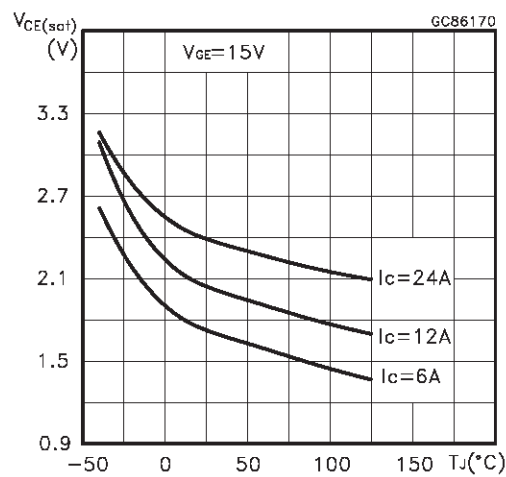
Transfer Characteristics



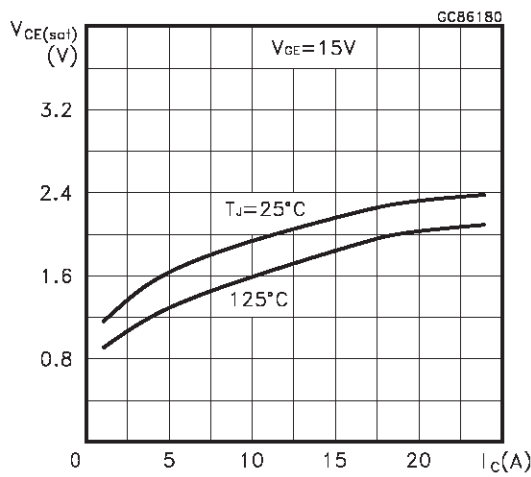
Transconductance



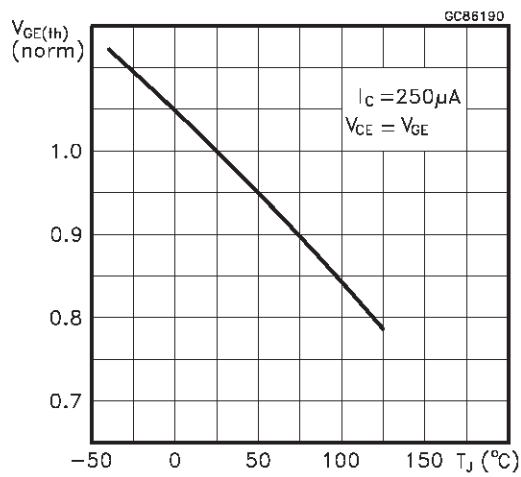
Collector-Emitter On Voltage vs Temperature



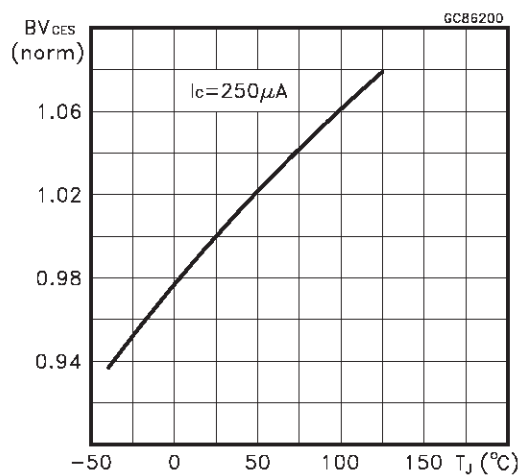
Collector-Emitter On Voltage vs Collector Current



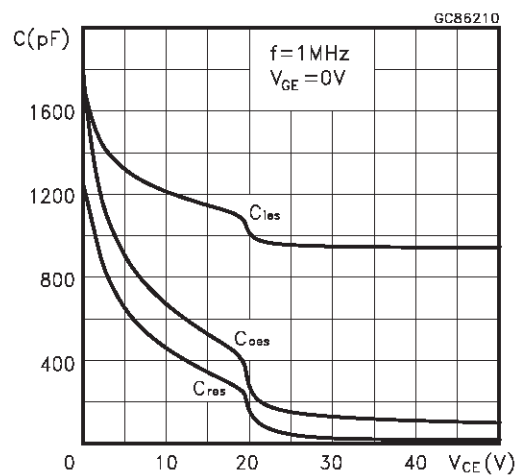
Gate Threshold vs Temperature



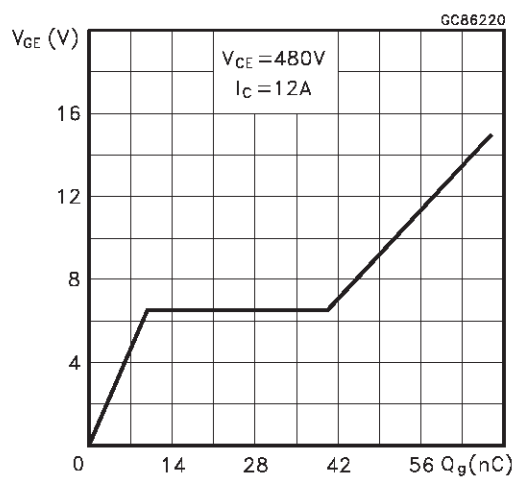
Normalized Breakdown Voltage vs Temperature



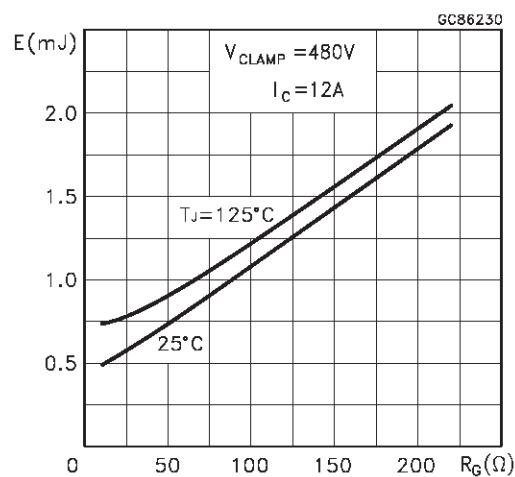
Capacitance Variations



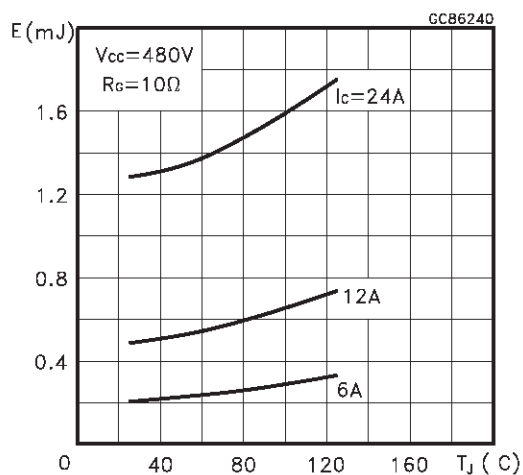
Gate Charge vs Gate-Emitter Voltage



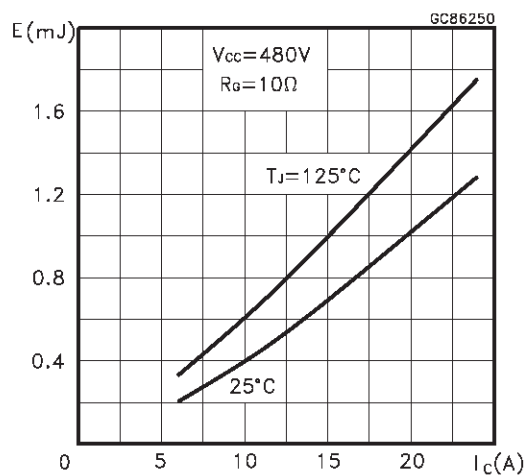
Total Switching Losses vs Gate Resistance



Total Switching Losses vs Temperature



Total Switching Losses vs Collector Current



Switching Off Safe Operating Area

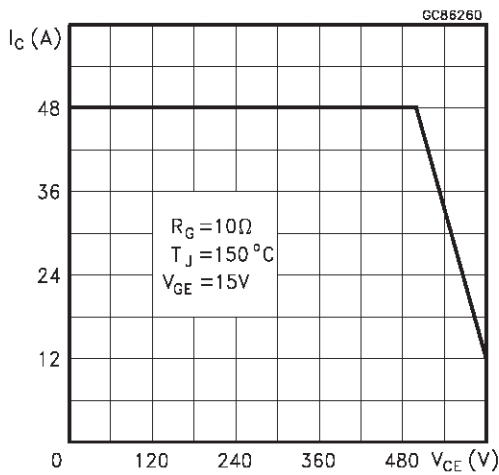


Fig. 1: Gate Charge test Circuit

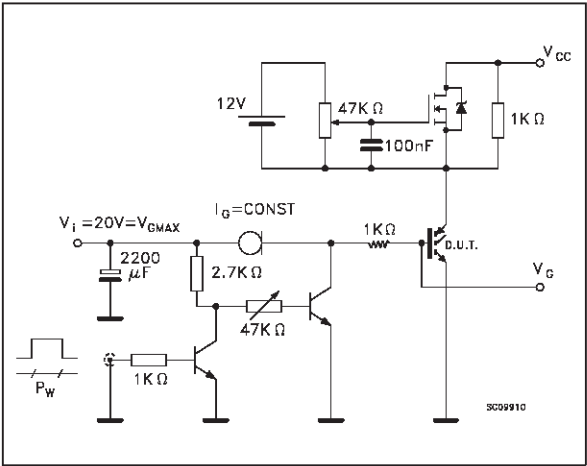


Fig. 2: Test Circuit For Inductive Load Switching

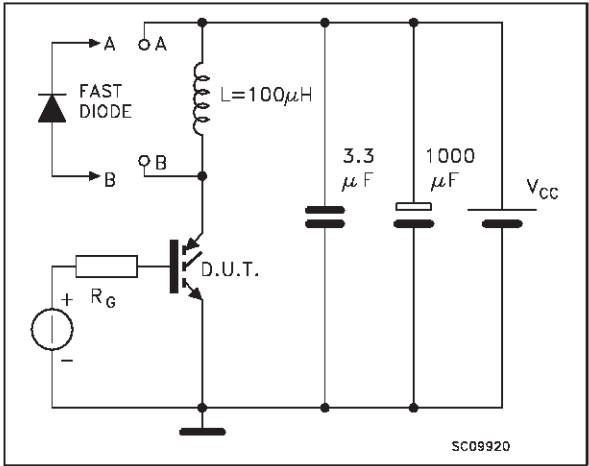
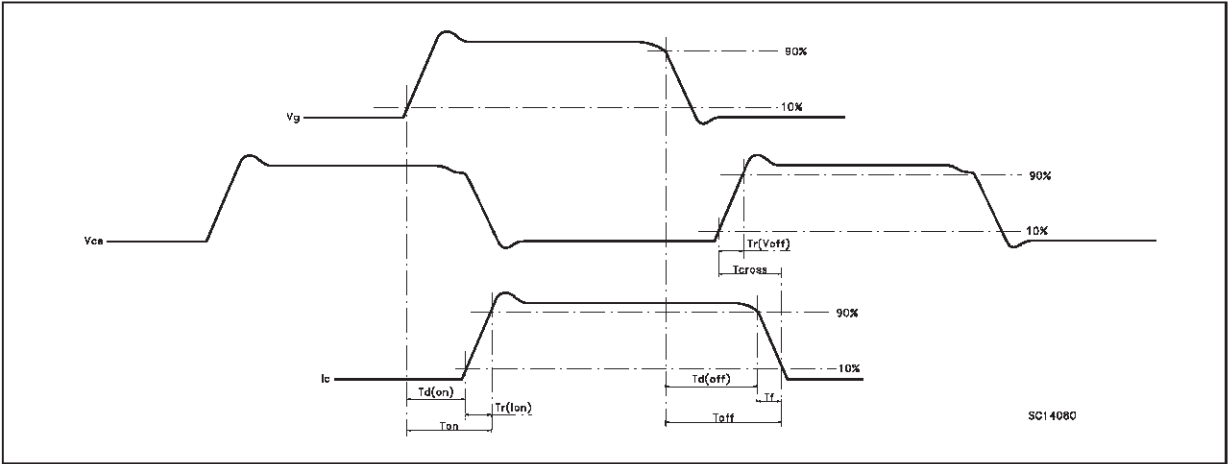
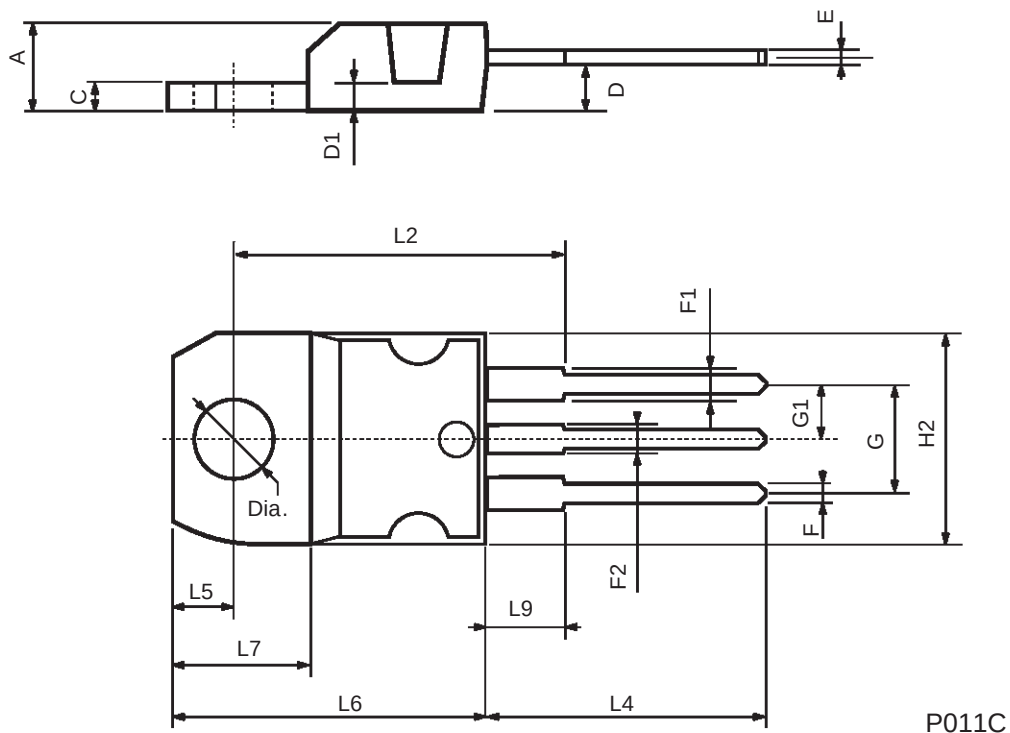


Fig. 3: Switching Waveforms



TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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